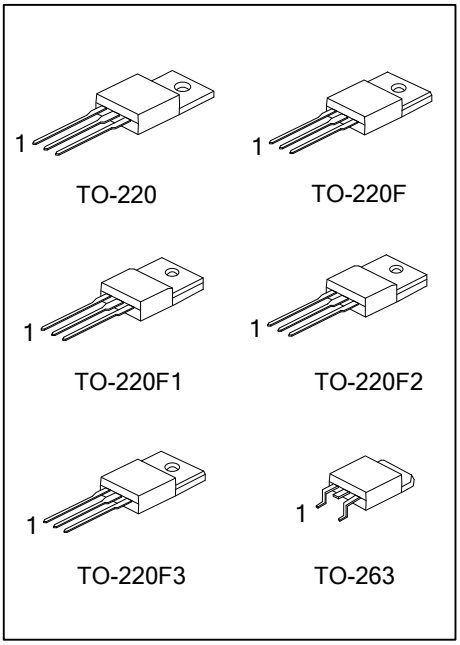
12N65K-MT

Power MOSFET

12A, 650V N-CHANNEL POWER MOSFET



■ DESCRIPTION

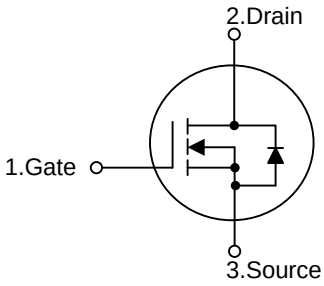
The UTC **12N65K-MT** are N-Channel enhancement mode power field effect transistors (MOSFET) which are produced by using UTC's proprietary, planar stripe and DMOS technology.

These devices are suited for high efficiency switch mode power supply. To minimize on-state resistance, provide superior switching performance and withstand high energy pulse in the avalanche and commutation mode, the advanced technology has been especially tailored.

■ FEATURES

* $R_{DS(ON)} \leq 0.7\Omega$ @ V_{GS}=10V, I_D=6.0A
* Fast switching capability
* Avalanche energy specified
* Improved dv/dt capability, high ruggedness

■ SYMBOL



■ ORDERING INFORMATION

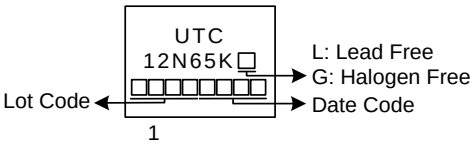
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
12N65KL-TA3-T	12N65KG-TA3-T	TO-220	G	D	S	Tube
12N65KL-TF1-T	12N65KG-TF1-T	TO-220F1	G	D	S	Tube
12N65KL-TF2-T	12N65KG-TF2-T	TO-220F2	G	D	S	Tube
12N65KL-TF3-T	12N65KG-TF3-T	TO-220F	G	D	S	Tube
12N65KL-TF3T-T	12N65KG-TF3T-T	TO-220F3	G	D	S	Tube
12N65KL-TQ2-T	12N65KG-TQ2-T	TO-263	G	D	S	Tube
12N65KL-TQ2-R	12N65KG-TQ2-R	TO-263	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

12N65KG-TA3-T
(1)Packing Type
(2)Package Type
(3)Green Package

(1) T: Tube, R: Tape Reel
(2) TA3: TO-220, TF1: TO-220F1, TF2: TO-220F2
TF3: TO-220F, TF3T: TO-220F3, TQ2: TO-263
(3) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	650	V
Gate-Source Voltage		V_{GSS}	±30	V
Drain Current	Continuous	I_D	12	A
	Pulsed (Note 2)	I_{DM}	48	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	400	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	2.7	V/ns
Power Dissipation	TO-220/TO-263	P_D	225	W
	TO-220F/TO-220F1/ TO-220F2/TO-220F3		51	W
Junction Temperature		T_J	+150	°C
Operating Temperature		T_{OPR}	-55 ~ +150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating : Pulse width limited by maximum junction temperature
3. L =5.55mH, I_{AS} = 12A, V_{DD} = 50V, R_G = 25Ω, Starting T_J = 25°C
4. I_{SD} ≤ 12A, di/dt ≤200A/μs, V_{DD} ≤BV_{DSS} Starting T_J = 25°C

■ THERMAL DATA

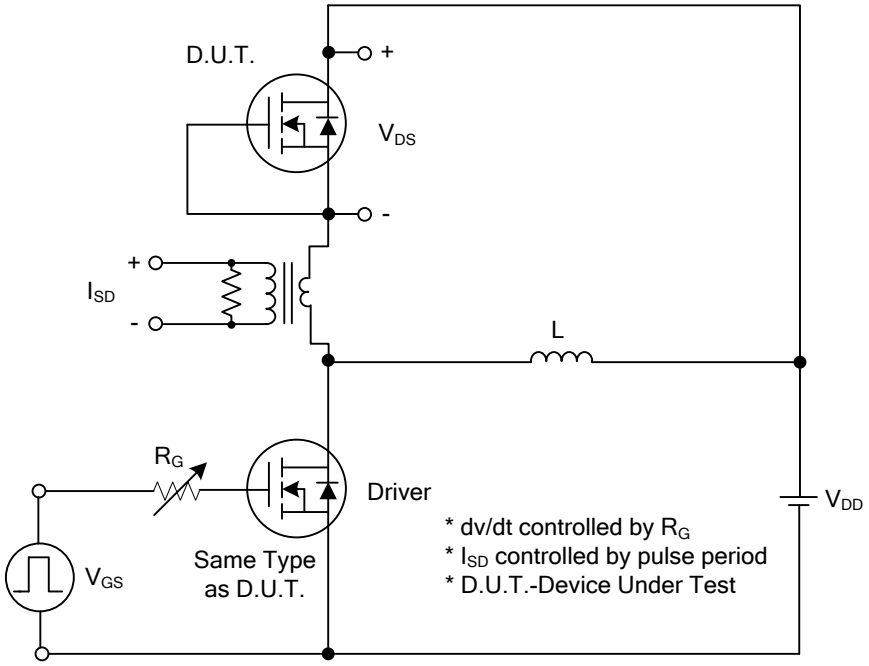
PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient		θ_{JA}	62.5	°C/W
Junction to Case	TO-220/TO-263	θ_{JC}	0.56	°C/W
	TO-220F/TO-220F1/ TO-220F2/TO-220F3		2.43	°C/W

■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

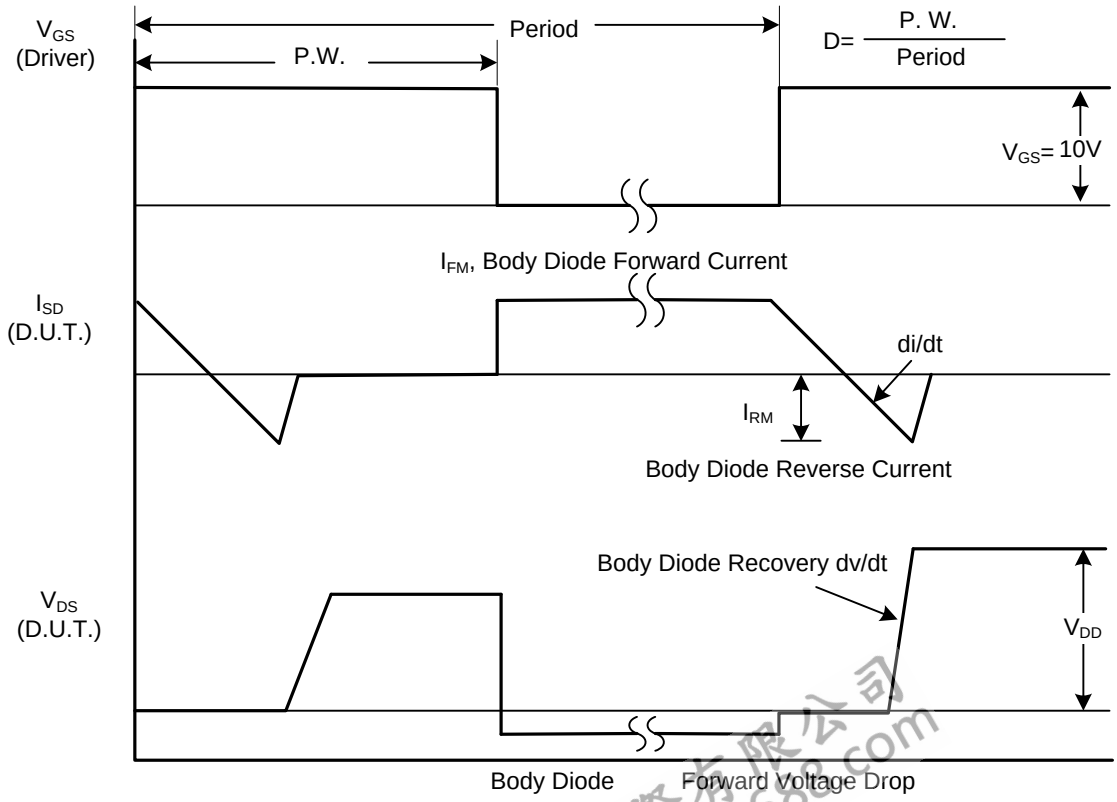
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D=250μA	650			V
Drain-Source Leakage Current	I_{DSS}	V_{DS}=650V, V_{GS}=0V			10	μA
Gate-Source Leakage Current	I_{GSS}	V_{GS}=±30V, V_{DS}=0V			±100	nA
Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS}/\triangle T_J$	I_D=250μA, Referencedto25°C		0.7		V/°C
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=250μA	2.0		4.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=6.0A		0.60	0.7	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ISS}	V_{DS}=25V, V_{GS}=0V, f=1MHz		2126		pF
Output Capacitance	C_{OSS}			170		pF
Reverse Transfer Capacitance	C_{RSS}			5		pF
SWITCHING CHARACTERISTICS						
Total Gate Charge	Q_G	V_{DS}=100V, V_{GS}=10V, I_D=12A, I_G=1mA (Note1,2)		53		nC
Gate-Source Charge	Q_{GS}			10		nC
Gate-Drain Charge	Q_{GD}			7		nC
Turn-On Delay Time	$t_{D(ON)}$	V_{DD}=100V, V_{GS}=10V, I_D=12A R_G=25Ω (Note1,2)		26		ns
Turn-On Rise Time	t_R			18		ns
Turn-Off Delay Time	$t_{D(OFF)}$			130		ns
Turn-Off Fall Time	t_F			31		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Continuous Drain-Source Diode Forward Current	I_S				12	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}				48	A
Drain-Source Diode Forward Voltage	V_{SD}	I_S=12A, V_{GS}=0V			1.4	V
Reverse Recovery Time	t_{rr}	I_S=12A, V_{GS}=0V di/dt=100A/μs(Note1)		415		ns
Reverse Recovery Charge	Q_{rr}			5.5		μC

Notes: 1. Pulse Test : Pulse width ≤300μs, Duty cycle ≤ 2%
2. Essentially independent of operating temperature

■ TEST CIRCUITS AND WAVEFORMS

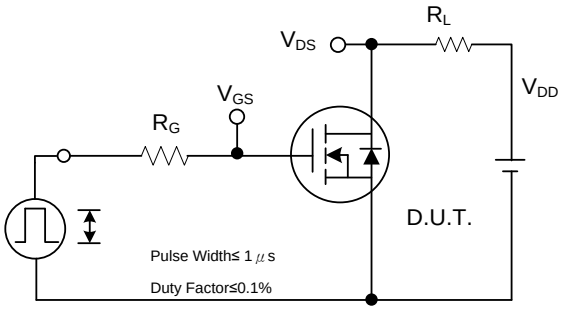


Peak Diode Recovery dv/dt Test Circuit

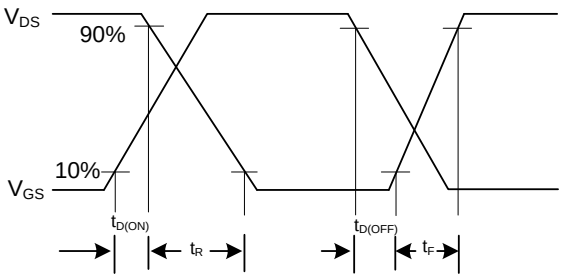


Peak Diode Recovery dv/dt Waveforms

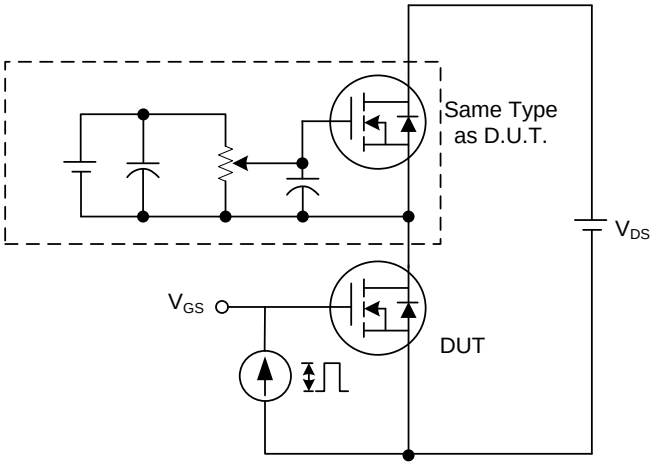
■ TEST CIRCUITS AND WAVEFORMS



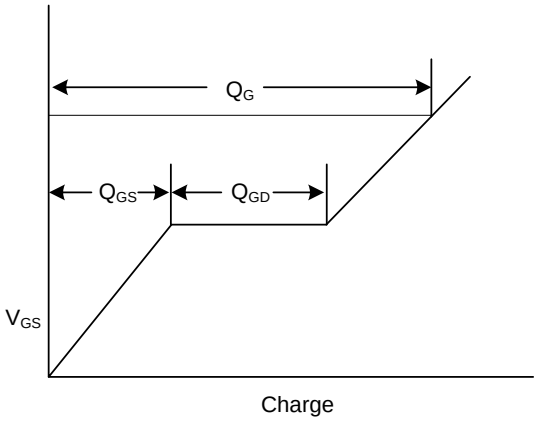
Switching Test Circuit



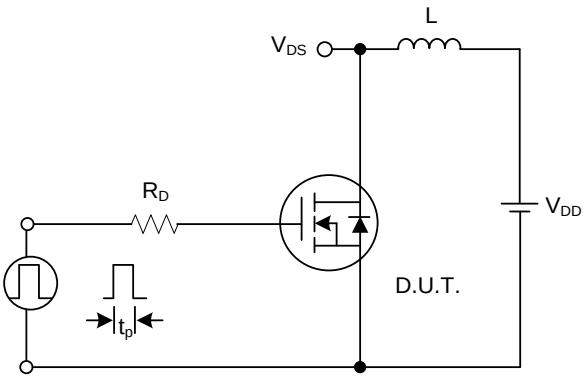
Switching Waveforms



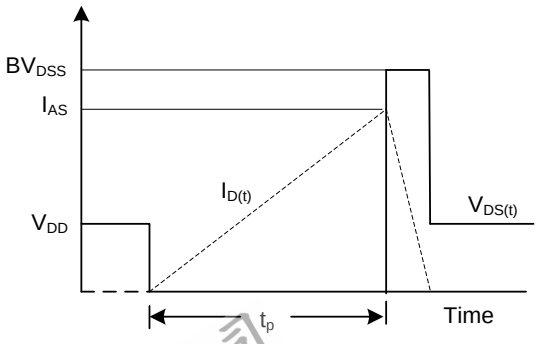
Gate Charge Test Circuit



Gate Charge Waveform



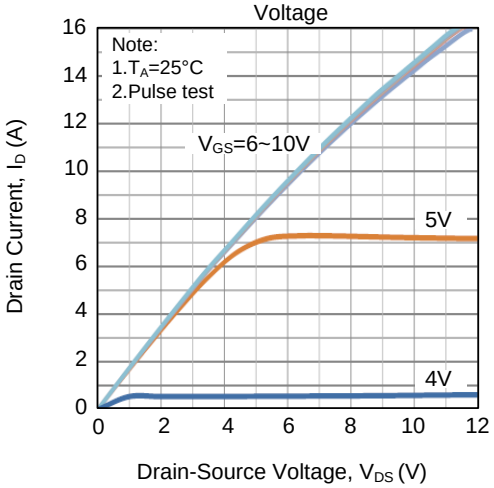
Unclamped Inductive Switching Test Circuit



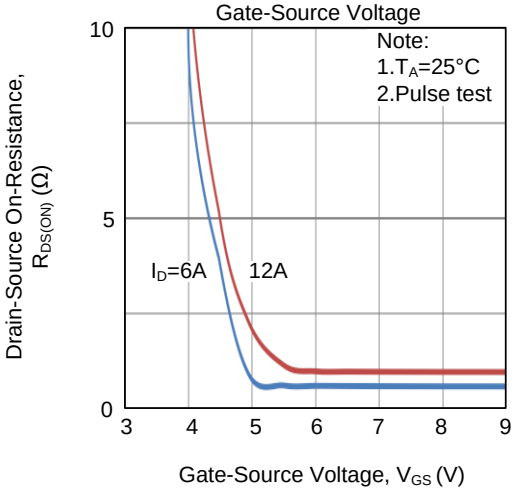
Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS

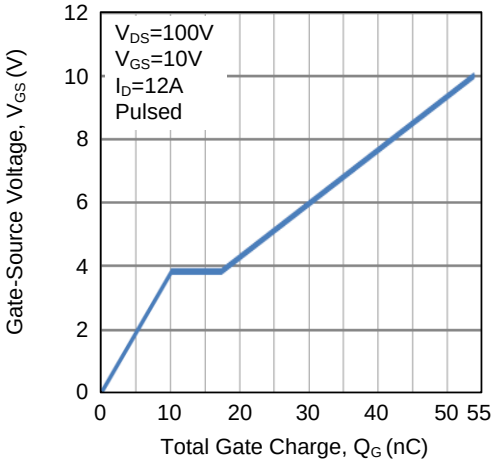
Drain Current vs. Drain-Source Voltage



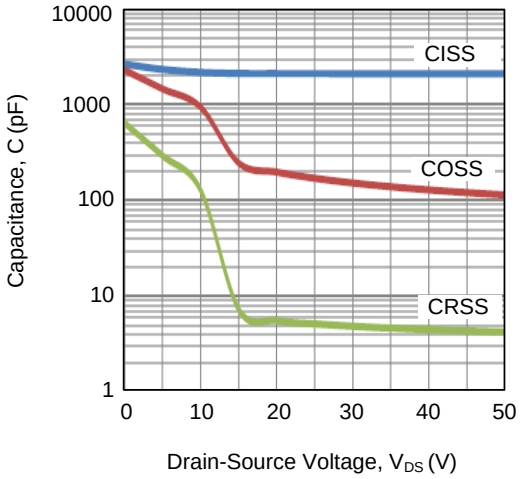
Drain-Source On-Resistance vs. Gate-Source Voltage



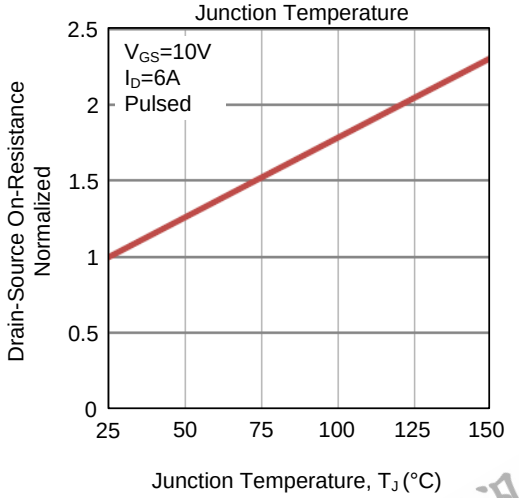
Gate Charge Characteristics



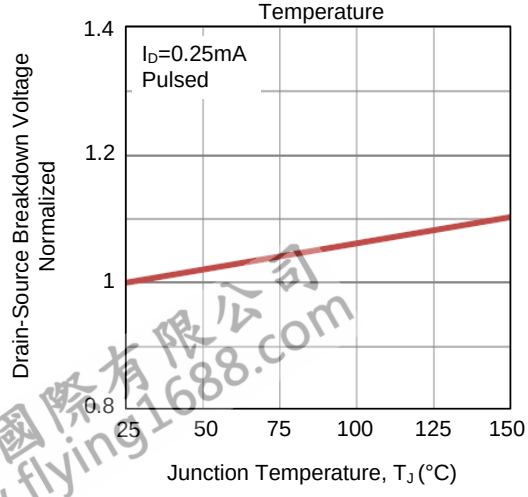
Capacitance Characteristics



Drain-Source On-Resistance vs. Junction Temperature

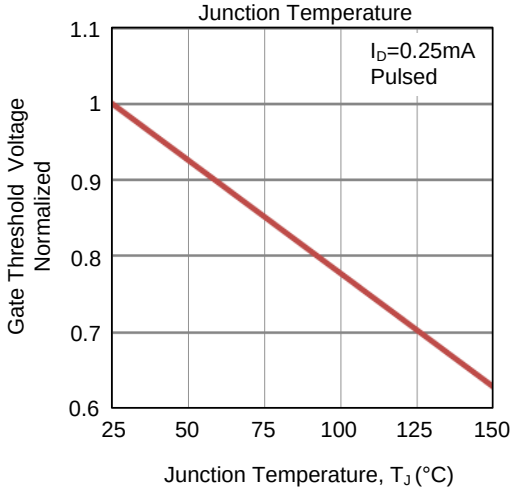


Breakdown Voltage vs. Junction Temperature

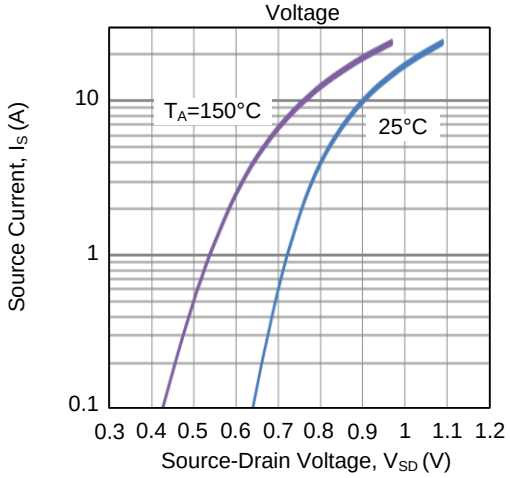


■ TYPICAL CHARACTERISTICS (Cont.)

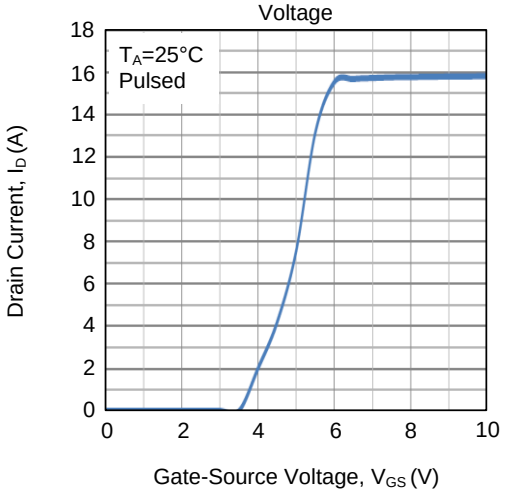
Gate Threshold Voltage vs. Junction Temperature



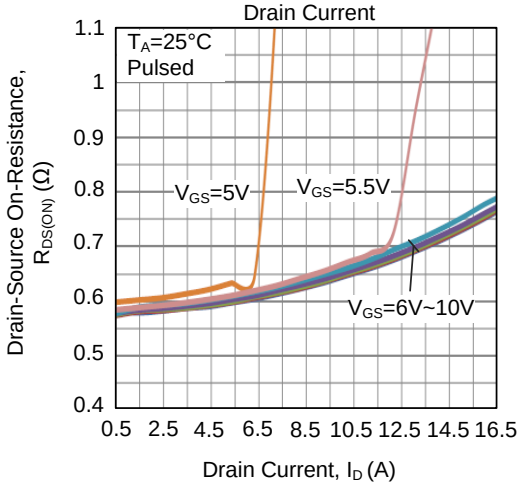
Source Current vs. Source-Drain Voltage



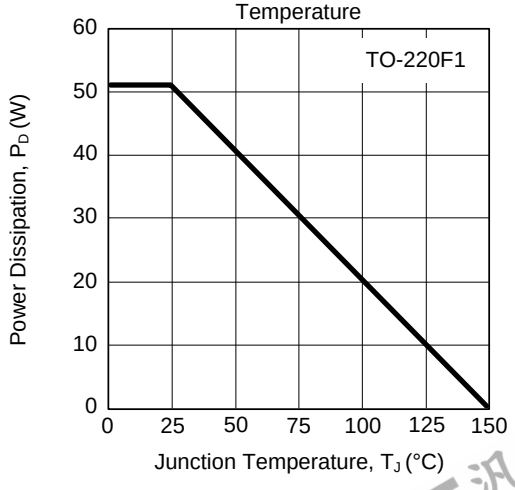
Drain Current vs. Gate-Source Voltage



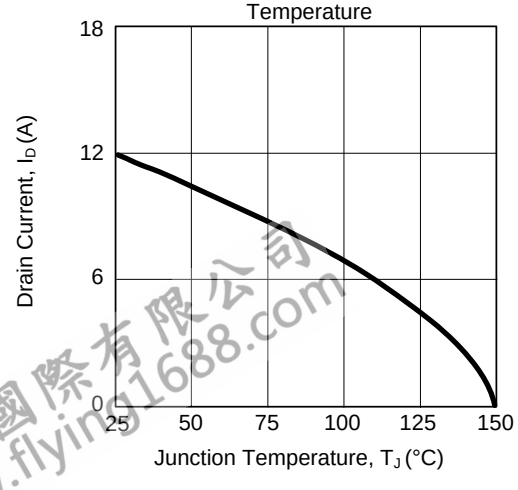
Drain-Source On-Resistance vs. Drain Current



Power Dissipation vs. Junction Temperature



Drain Current vs. Junction Temperature



■ TYPICAL CHARACTERISTICS (Cont.)